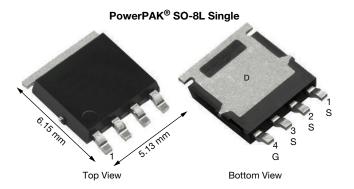
SQJ860EP

www.vishay.com

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	40
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0060
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0073
I _D (A)	60
Configuration	Single
Package	PowerPAK SO-8L

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

N-Channel MOSFET

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ROHS COMPLIANT HALOGEN FREE

ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unless	s otherwise noted	i)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	40	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current	$T_{C} = 25 \ ^{\circ}C \ ^{a}$	I-	60	
Continuous Drain Current	T _C = 125 °C	I _D	36	
Continuous Source Current (Diode Conductio	n)	I _S	43	А
Pulsed Drain Current ^b	I _{DM}	120		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	32	
Single Pulse Avalanche Energy	L = 0.1 MH	E _{AS}	51	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	PD	48	W
Maximum Power Dissipation ~	T _C = 125 °C	۳D	16	vv
Operating Junction and Storage Temperature	T _J , T _{stg}	-55 to +175	°C	
Soldering Recommendations (Peak Temperat	ure) ^{d, e}		260	C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	70	°C/W
Junction-to-Case (Drain)		R _{thJC}	3.1	0/10

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static				•		•	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		40	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μΑ	1.5	2.0	2.5	v
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V _{DS} = 40 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		V _{GS} = 10 V	I _D = 10 A	-	0.0050	0.0060	
		V _{GS} = 4.5 V	I _D = 8 A	-	0.0061	0.0073	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.0099	
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	0.0122	
Forward Transconductance b	g fs	V _{DS}	= 15 V, I _D = 10 A	-	78	-	S
Dynamic ^b					•		
Input Capacitance	C _{iss}			-	2020	2700	
Output Capacitance	Coss	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	265	350	pF
Reverse Transfer Capacitance	C _{rss}			-	110	150	
Total Gate Charge ^c	Qg			-	34	55	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_D = 20 \text{ A}$	-	6	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	7	-	
Gate Resistance	R _g	f = 1 MHz		1.3	2.7	4.5	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	10	20	
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = 20 \ V, \ R_{L} = 2 \ \Omega \\ I_{D} \cong 10 \ A, \ V_{GEN} = 10 \ V, \ R_{g} = 1 \ \Omega \end{array}$		-	5	10	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	30	50	
Fall Time ^c	t _f			-	5	10	
Source-Drain Diode Ratings and Charac	teristics ^b	•			•		
Pulsed Current ^a	I _{SM}			-	-	120	А
Forward Voltage	V _{SD}	I _F = 10 A, V _{GS} = 0		-	0.8	1.2	V
Body diode reverse recovery time	t _{rr}			-	29	60	ns
Body diode reverse recovery charge	Q _{rr}	1	A -11/-11 - 100 A/	-	27	60	nC
Reverse recovery fall time	ta	I _F = 5 /	A, di/dt = 100 A/µs	-	17	-	
Reverse recovery rise time	t _b	1		-	11	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			_	-1.8	-4	А

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

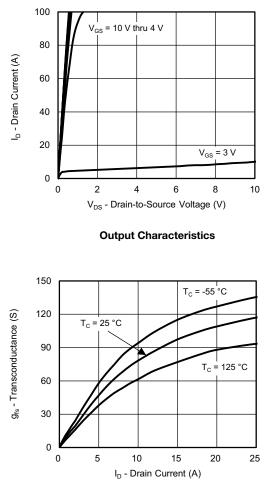
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

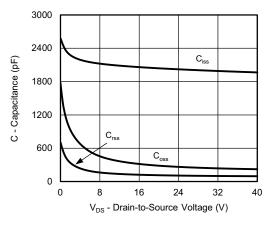
2



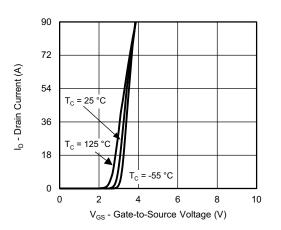
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



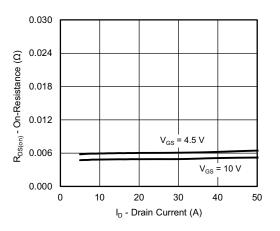
Transconductance



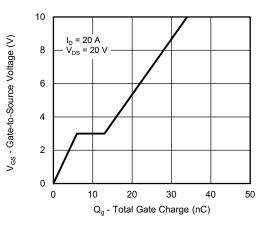




Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

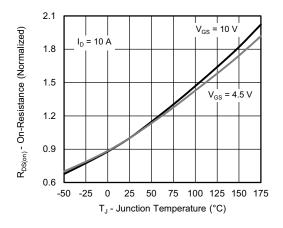
S16-1947-Rev. A, 26-Sep-16

3 s. contact: automostechsur

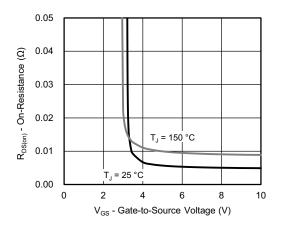
For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



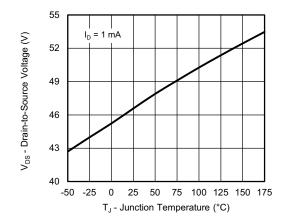
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



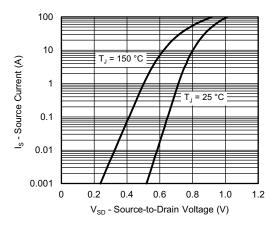
On-Resistance vs. Junction Temperature



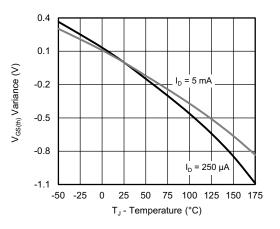
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage

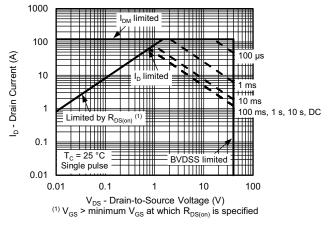


Threshold Voltage

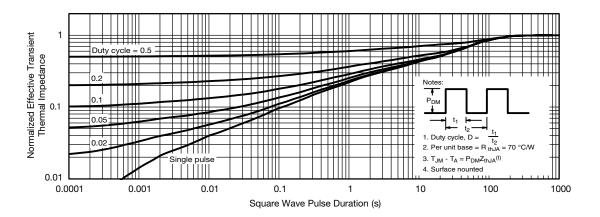
4



THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)









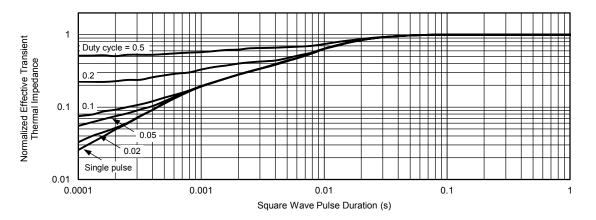


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

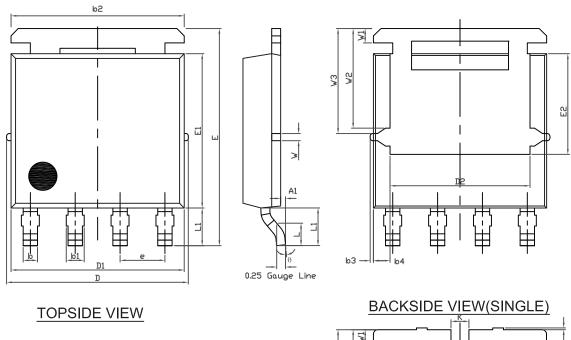
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

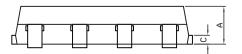
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

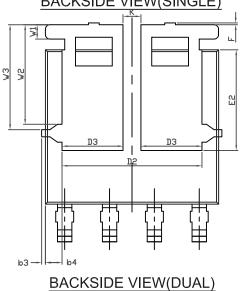
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75516.











Package Information



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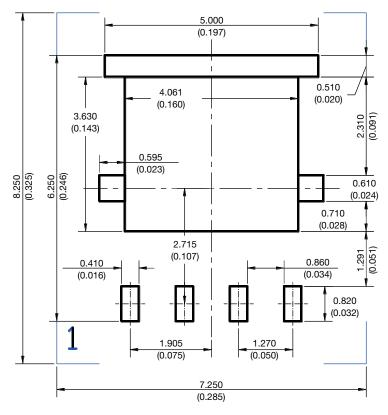
DIM		MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094	•		0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC	•	0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51	•	0.020				
W		0.23			0.009			
W1	0.41			0.016				
W2	2.82		0.111					
W3		2.96		0.117				
q	0°	-	10°	0°	-	10°		

Note

• Millimeters will gover



RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



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